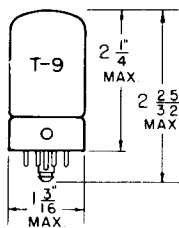


**TUNG-SOL**

BEAM PENTODE



GLASS BULB

COATED FILAMENT

**SERIES FILAMENT**

$E_f$  APPLIED BETWEEN PINS 1 & 8

$E_{g1}$  REFERRED TO PIN 8

2.8 VOLTS  
110 MA.

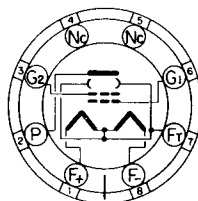
**PARALLEL FILAMENT**

$E_f$  APPLIED BETWEEN PIN 7 AND PINS 1 & 8 TIED TOGETHER

$E_{g1}$  REFERRED TO PIN 7

1.4 VOLTS  
220 MA.

DC



BOTTOM VIEW

LOCK-IN 8 PIN BASE

688

A SHUNTING RESISTOR MUST BE CONNECTED BETWEEN PINS 1 AND 7 FOR SERIES-FILAMENT OPERATION. ITS VALUE SHOULD BE SUCH THAT THE VOLTAGE ACROSS THE SHUNTED SECTION IS EQUAL TO THE VOLTAGE BETWEEN PINS 7 AND 8. AN ADDITIONAL SHUNTING RESISTOR MAY BE NECESSARY BETWEEN PINS 1 AND 8 IF OTHER TUBES USED IN SERIES-FILAMENT ARRANGEMENT CONTRIBUTE TO THE FILAMENT CURRENT OF THE 3D6/1299.

ANY MOUNTING POSITION

THE 3D6/1299 IS A FILAMENTARY TYPE BEAM POWER AMPLIFIER FOR USE IN LIGHT AND PORTABLE EQUIPMENT USING THE LOCK-IN CONSTRUCTION. IN AUDIO SERVICE, IT WILL DELIVER RELATIVELY LARGE AMOUNTS OF AUDIO POWER. IN RF AMPLIFIER SERVICE IT WILL DELIVER A POWER OUTPUT OF 1.4 WATTS AT 50 MEGACYCLES.

DIRECT INTERELECTRODE CAPACITANCES

	WITH SHIELD <sup>A</sup>	WITHOUT SHIELD <sup>B</sup>	
GRID TO PLATE: ( $G_1$ TO P)	0.3	0.3	$\mu f$
INPUT: $G_1$ TO ( $F+G_2+B_P+S$ )	7.5	7.5	$\mu f$
OUTPUT: P TO ( $F+G_2+B_P+S$ )	6.5	5.5	$\mu f$

<sup>A</sup> WITH EXTERNAL SHIELD CONNECTED TO F-. PIN 5 CONNECTED TO FILAMENT CENTER TAP.

<sup>B</sup> PIN 5 CONNECTED TO FILAMENT CENTER TAP.

RATINGS

INTERPRETED ACCORDING TO RMA STANDARD M8-210

	SERIES FILAMENT	PARALLEL FILAMENT	
MAXIMUM FILAMENT VOLTAGE	3.5	1.75	VOLTS
MINIMUM FILAMENT VOLTAGE	2.8	1.4	VOLTS
MAXIMUM PLATE VOLTAGE	180	180	VOLTS
MAXIMUM GRID #2 VOLTAGE	135	135	VOLTS
MAXIMUM PLATE DISSIPATION	4.5	4.5	WATTS
MAXIMUM GRID #2 DISSIPATION	0.9	0.9	WATT
MAXIMUM CATHODE CURRENT	30	30	MA.

CONTINUED ON FOLLOWING PAGE

## TUNG-SOL

CONTINUED FROM PRECEDING PAGE

## TYPICAL OPERATING CONDITIONS AND CHARACTERISTICS

AF POWER AMPLIFIER - CLASS A<sub>1</sub>

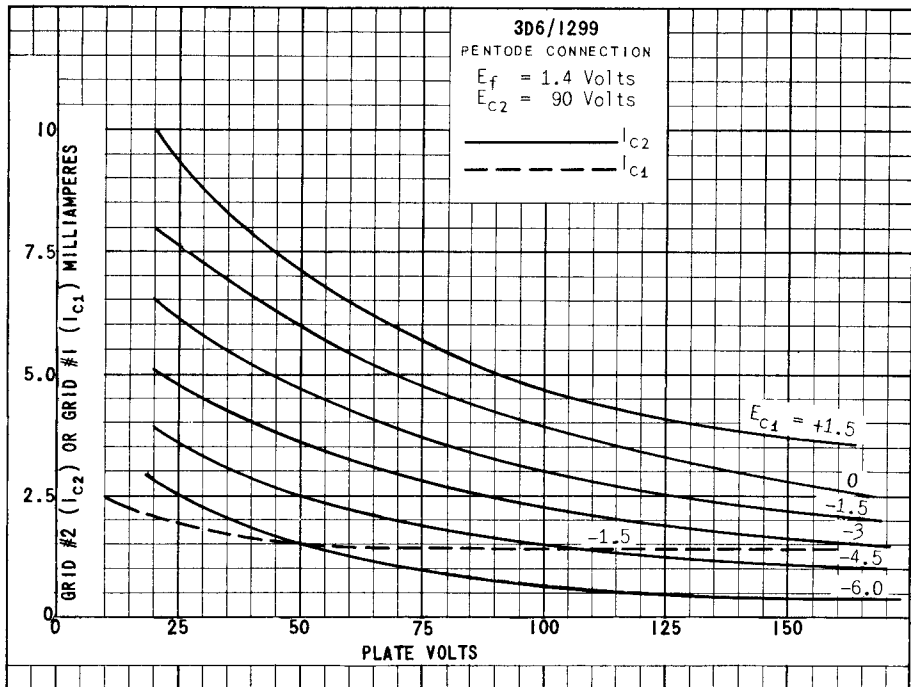
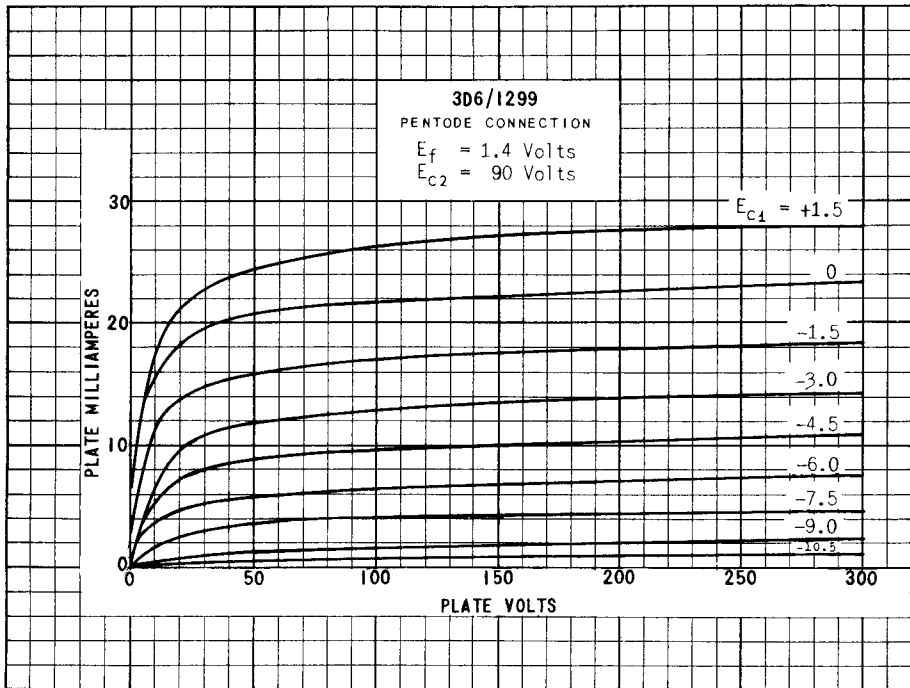
VALUES FOR SERIES-FILAMENT OPERATION WILL BE APPROXIMATELY THE SAME AS FOR PARALLEL-FILAMENT OPERATION.

FILAMENT VOLTAGE	1.4	1.4	1.4	VOLTS
FILAMENT CURRENT	220	220	220	MA.
PLATE VOLTAGE	90	135	150	VOLTS
GRID #2 VOLTAGE	90	90	90	VOLTS
GRID #1 VOLTAGE	-4.5	-4.5	-4.5	VOLTS
PEAK AF SIGNAL VOLTAGE	4.5	4.5	4.5	VOLTS
TRANSCONDUCTANCE	2 400	2 400	2 400	μMHOS
ZERO-SIGNAL PLATE CURRENT	9.5	9.8	9.9	MA.
ZERO-SIGNAL GRID #2 CURRENT	1.6	1.2	1.0	MA.
MAXIMUM SIGNAL PLATE CURRENT	8.5	9.8	10.2	MA.
MAXIMUM SIGNAL GRID #2 CURRENT	3.2	2	1.8	MA.
LOAD RESISTANCE	8 000	12 000	14 000	OHMS
TOTAL HARMONIC DISTORTION	5	5	5	PERCENT
POWER OUTPUT	270	500	600	MW.

## RF POWER AMPLIFIER AT 50 MC - CLASS C

FILAMENT VOLTAGE	1.4	VOLTS
FILAMENT CURRENT	220	MA.
PLATE VOLTAGE	150	VOLTS
GRID #2 VOLTAGE	135	VOLTS
GRID #1 VOLTAGE (APPROX.) <sup>C</sup>	-20	VOLTS
PEAK RF GRID #1 VOLTAGE	55	VOLTS
PLATE CURRENT	23	MA.
GRID #2 CURRENT	6	MA.
GRID #1 CURRENT	1	MA.
TOTAL DC CATHODE CURRENT (NOT TO EXCEED 30 MA.)	30	MA.
RF POWER INPUT	0.25	WATT
RF POWER OUTPUT	1.4	WATTS

<sup>C</sup> OBTAINED FROM A FIXED SOURCE OR FROM THE DROP ACROSS A SUITABLE GRID RESISTOR.



PRINTED IN U. S. A.

PLATE  
2204  
JUNE 1,  
1949

